



#### 100V PNP HIGH VOLTAGE TRANSISTOR IN TO252 (DPAK)

### **Description**

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

#### **Features**

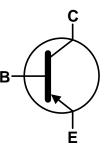
- BV<sub>CFO</sub> > -100V
- I<sub>C</sub> = -3A High Continuous Collector Current
- I<sub>CM</sub> = -5A Peak Pulse Current
- Ideal for Power Switching or Amplification Applications
- Complementary NPN Type: MJD31CUQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

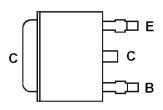
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202. Method 208 @3
- Weight: 0.34 grams (Approximate)







**Device Schematic** 



Pin Out Configuration Top View

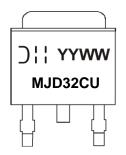
### Ordering Information (Notes 4 & 5)

I	Part number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	MJD32CUQ-13	Automotive	MJD32CU	13	16	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**





# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-120	V
Collector-Emitter Voltage	$V_{CEO}$	-100	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	Ic	-3	А
Peak Pulse Collector Current	I <sub>CM</sub>	-5	А
Continuous Base Current	lΒ	-1	А
Power Dissipation	$P_{D}$	15	W

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	(Note 6)		3.9	
Power Dissipation	(Note 7)	P <sub>D</sub>	2.1	W
	(Note 8)		1.6	
	(Note 6)		32	
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ heta JA}$	59	°C/W
	(Note 8)		80	C/VV
Thermal Resistance, Junction to Leads	(Note 9)	$R_{ heta JL}$	3.6	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

# ESD Ratings (Note 10)

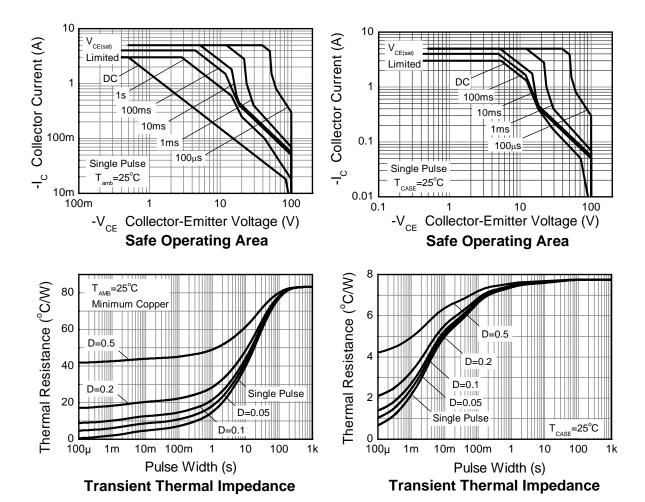
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as note (6), except mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# **Thermal Characteristics**





# **Electrical** Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

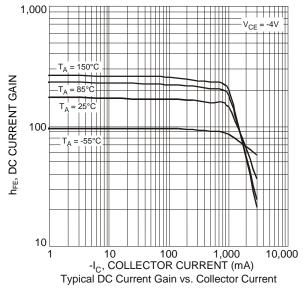
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-120	-	I	V	$I_C = -20\mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	-100	-	I	V	$I_C = -30mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-	I	V	$I_E = -100 \mu A$
Collector-Base Cut-off Current	I <sub>CBO</sub>	-	-	-1	μΑ	V <sub>CB</sub> = -100V
Collector Cut-off Current	I <sub>CEO</sub>	-	-	-1	μΑ	$V_{CE} = -60V$
Collector Cut-off Current	I <sub>CES</sub>	-	-	-1	μΑ	V <sub>CE</sub> = -100V
Emitter Cut-off Current	I <sub>EBO</sub>	-	_	-1	μΑ	V <sub>EB</sub> = -5V
Oallantan Farittan Oatsmatian Maltana	V <sub>CE(sat)</sub>	_	-	-300	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA
Collector-Emitter Saturation Voltage (Note 11)		_	-	-500	mV	$I_C = -2A$ , $I_B = -200mA$
(Note 11)		-	-	-700	mV	$I_C = -3A$ , $I_B = -375mA$
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	_	-	-1.2	V	I <sub>C</sub> = -2A, I <sub>B</sub> = -200mA
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	-	-	-950	mV	$I_C = -1A$ , $V_{CE} = -2V$
Base-Ellinter Fulli-Oli Voltage (Note 11)		-	1	-1.4	V	$I_C = -3A$ , $V_{CE} = -4V$
DC Current Gain (Note 11)	h <sub>FE</sub>	25		1		$V_{CE} = -4V, I_{C} = -1A$
Do Current Gain (Note 11)		10		50	_	$V_{CE} = -4V$ , $I_C = -3A$
Current Signal Current Gain	H <sub>fe</sub>	20	-	I	-	$V_{CE} = -10V$ , $I_{C} = -0.5A$ , $f = 1kHz$
Current Gain-Bandwidth Product	f <sub>T</sub>	3.0	-	I	MHz	$I_C = -0.5A$ , $V_{CE} = -10V$ , $f = 1MHz$

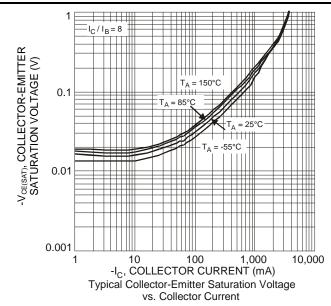
Note: 11. Mea

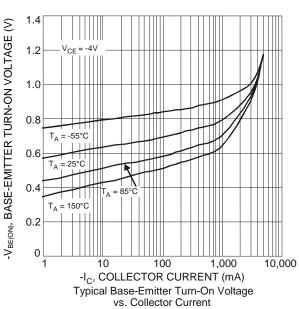
11. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s.$  Duty cycle  $\leq 2\%.$ 

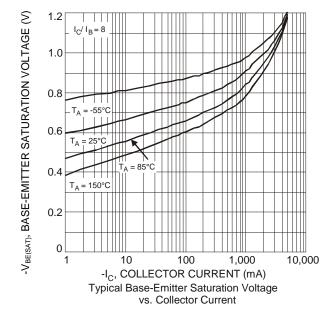


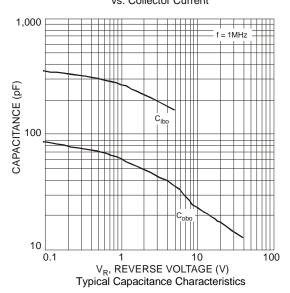
# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)









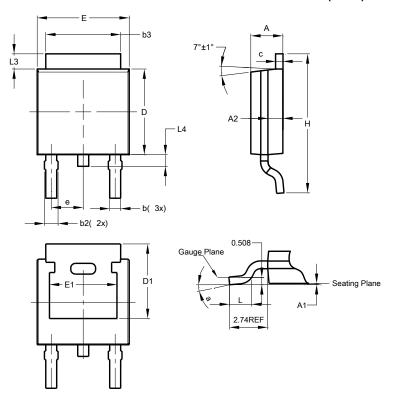




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO252 (DPAK)

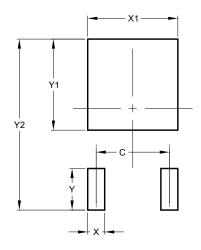


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A</b> 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
p	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
I	9.40	10.41	9.91		
٦	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO252 (DPAK)



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Υ	2.600
Y1	5.700
Y2	10.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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